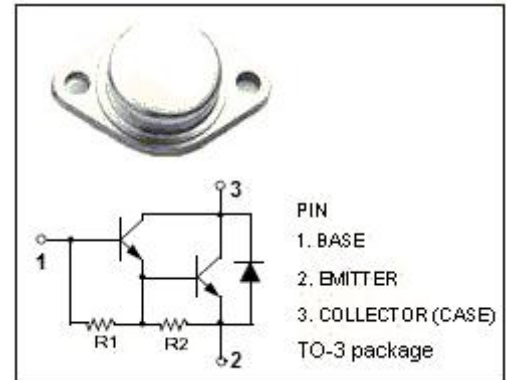


**isc Silicon NPN Darlington Power Transistor**
**2N6284**
**DESCRIPTION**

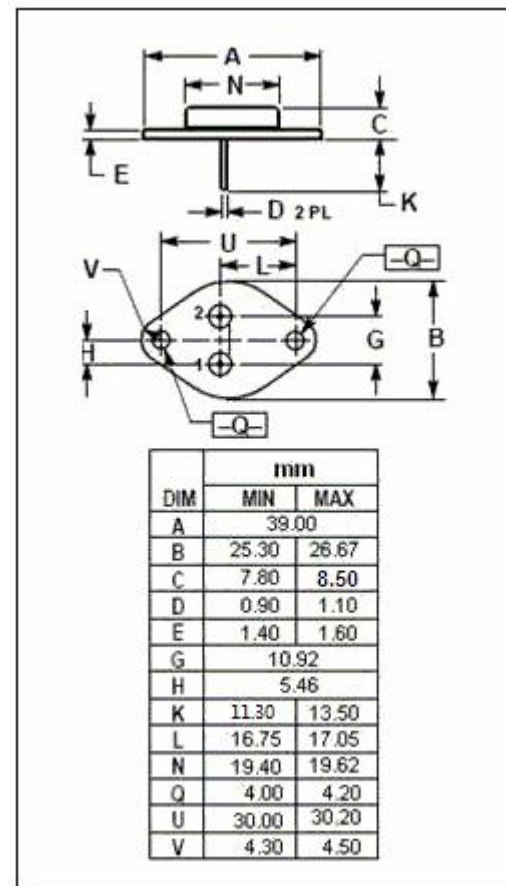
- Built-in Base-Emitter Shunt Resistors
- High DC current gain-  
 $h_{FE} = 750$  (Min) @  $I_C = 10$  A dc
- Collector-Emitter Sustaining Voltage-  
 $V_{CEO(SUS)} = 100V$  (Min)
- Complement to type 2N6287
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Intended for general purpose amplifier and low frequency switching applications, such as linear and switching industrial equipment.


**ABSOLUTE MAXIMUM RATINGS( $T_C = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current -Continuous	20	A
$I_{CP}$	Collector Current-Peak	40	A
$I_B$	Base Current	0.5	A
$P_C$	Collector Power Dissipation@ $T_C = 25^\circ C$	160	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-65~150	$^\circ C$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	ThermalResistance, Junction to Case	1.09	$^\circ C/W$

**isc Silicon NPN Darlingtion Power Transistor****2N6284****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 50\text{mA}$ ; $I_B= 0$	100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C= 10\text{A}$ ; $I_B= 40\text{mA}$		2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C= 20\text{A}$ ; $I_B= 200\text{mA}$		3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation voltage	$I_C= 20\text{A}$ ; $I_B= 200\text{mA}$		4.0	V
$V_{BE(on)}$	Base-Emitter On voltage	$I_C= 10\text{A}$ ; $V_{CE}= 3\text{V}$		2.8	V
$I_{CEO}$	Collector Cutoff current	$V_{CE}= 50\text{V}$ ; $I_B=0$		1.0	mA
$I_{CEX}$	Collector Cutoff current	$V_{CE}= 100\text{V}$ ; $V_{BE(off)}= 1.5\text{V}$ $V_{CE}= 100\text{V}$ ; $V_{BE(off)}= 1.5\text{V}$ , $T_C=150^\circ\text{C}$		0.5 5.0	mA
$I_{EBO}$	Emitter Cut-off current	$V_{EB}= 5\text{V}$ ; $I_C= 0$		2.0	mA
$h_{FE-1}$	DC Current Gain	$I_C= 10\text{A}$ ; $V_{CE}= 3\text{V}$	750	18000	
$h_{FE-2}$	DC Current Gain	$I_C= 20\text{A}$ ; $V_{CE}= 3\text{V}$	100		
$C_{OB}$	Output Capacitance	$I_E=0$ ; $V_{CB}= 10\text{V}$ ; $f_{test}= 1.0\text{MHz}$		400	pF

**NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.